

Brief Description

The ZSPM4521 is a DC/DC synchronous switching lithium-ion (Li-Ion) battery charger with fully integrated power switches, internal compensation, and full fault protection. It uses a temperature-independent photovoltaic maximum power point tracking (MPPT) function to optimize power output from the source during Full-Charge Constant-Current (CC) Mode. Its switching frequency of 1MHz enables the use of small filter components, resulting in smaller board space and reduced bill-of material costs.

During Full-Charge Constant-Current Mode, the duty cycle is controlled by the MPPT regulator. Once the battery's termination voltage is reached, the regulator operates in Constant Voltage Mode. In this mode, the ZSPM4521 modulates the charging current until the battery reaches full charge. When the regulator is disabled (the EN pin is low), the device draws 10µA (typical) quiescent current (Disabled Mode).

The ZSPM4521 includes supervisory reporting through the NFLT (inverted fault) open-drain output to interface other components in the system. Device programming is achieved by an I^2C^{TM*} interface through the SCL and SDA pins.

Benefits

- Up to 1.5A of continuous output current in Full-Charge Constant Current (CC) Mode
- High efficiency up to 92% with typical loads

Features

- Temperature-independent photovoltaic maximum power tracking (MPPT) regulator
- VBAT reverse-current blocking
- Programmable temperature-compensated termination voltage: 3.94V to 4.18V ± 1%
- User programmable maximum charge current: 50mA to 1500mA
- Supervisor for V_{BAT} reported at the NFLT pin
- Input supply under-voltage lockout
- Full protection for VBAT over-current, overtemperature, VBAT over-voltage, and charging timeout
- · Charge status indication
- I²C[™] program interface with EEPROM registers

Related IDT Smart Power Products

- ZSPM4523 DC/DC Synchronous Switching Super Capacitor Charger With MPPT Regulator
- ZSPM4551 High-Efficiency Li-Ion Battery Charger
- ZSPM4121 Ultra-low Power Under-Voltage Switch
- ZSPM4141 Ultra-Low-Power Linear Regulator

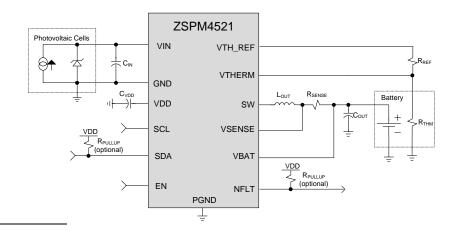
Physical Characteristics

- Wide input voltage range: 4.0V to 7.2V
- Junction operating temperature: -40°C to 125°C
- Package: 16-pin PQFN (4mm x 4mm)

ZSPM4521 Application Circuit

Available Support

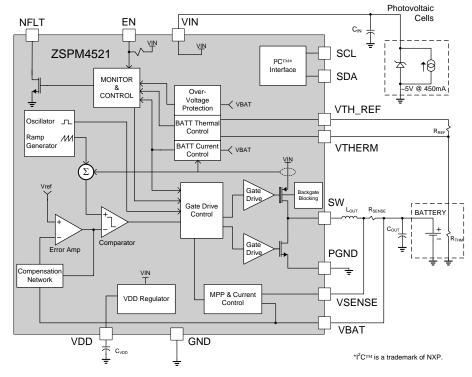
- Evaluation Kit
- Documentation



^{*} I²C™ is a trademark of NXP.



ZSPM4521 Block Diagram



Typical Applications

- Portable solar chargers
- Off-grid systems
- Wireless sensor networks
- HVAC controls

Ordering Information

Ordering Code	Description	Package
ZSPM4521AA1W	ZSPM4521 High Efficiency Li-Ion Battery Charger for Photovoltaic Sources	16-pin PQFN / 7" Reel (1000 parts)
ZSPM4521AA1R	ZSPM4521 High Efficiency Li-Ion Battery Charger for Photovoltaic Sources	16-pin PQFN / 13" Reel (3300 parts)
ZSPM4521KIT	ZSPM4521 Evaluation Kit	Kit



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1 ZSPM4521 Characteristics

Important: Stresses beyond those listed under "Absolute Maximum Ratings" (section 1.1) may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to absolute—maximum—rated conditions for extended periods may affect device reliability.

1.1. Absolute Maximum Ratings

Over operating free-air temperature range unless otherwise noted.

Table 1.1 Absolute Maximum Ratings

Parameter	Value 1)	Unit
VIN, EN, NFLT, SCL, SDA, VTHERM, VTH_REF, VBAT, VSENSE	-0.3 to 8	V
SW	-1 to 8.8	V
VDD	-0.3 to 3.6	V
Operating Junction Temperature Range, T _J	-40 to 125	°C
Storage Temperature Range, T _{STOR}	-65 to 150	°C
Electrostatic Discharge – Human Body Model ²⁾	±2k	V
Electrostatic Discharge – Machine Model 2)	+/-200	V
Lead Temperature (soldering, 10 seconds)	260	°C
·		

¹⁾ All voltage values are with respect to network ground terminal.

1.2. Thermal Characteristics

Table 1.2 Thermal Characteristics

Parameter	Symbol	Value 1)	Unit			
Thermal Resistance Junction to Air 1)	θ_{JA}	50	°C/W			
1) Assumes a 4x4mm QFN-16 in 1 in² area of 2 oz. copper and 25°C ambient temperature.						

²⁾ ESD testing is performed according to the respective JESD22 JEDEC standard.



1.3. Recommended Operating Conditions

Table 1.3 Recommended Operating Conditions

Parameter	Symbol	Min	Тур	Max	Unit
Photovoltaic Input Operating Voltage at VIN Pin	V _{IN}	4.0	5.3	7.2	V
Sense Resistor	R _{SENSE}		50		mΩ
Output Filter Inductor Typical Value 1)	L _{OUT}		4.7		μH
Output Filter Capacitor Typical Value 2)	C _{OUT}		4.7		μF
Output Filter Capacitor ESR	C _{OUT-ESR}			100	mΩ
Input Supply Bypass Capacitor Value 3)	C _{IN}	3.3	10		μF
VDD Supply Bypass Capacitor Value 2)	C _{VDD}	70	100	130	nF
Operating Free Air Temperature	T _A	-40		85	°C
Operating Junction Temperature	TJ	-40		125	°C

¹⁾ For best performance, use an inductor with a saturation current rating higher than the maximum V_{BAT} load requirement plus the inductor current ripple.

1.4. Electrical Characteristics

Electrical characteristics $T_J = -40$ °C to 125°C, VIN = 5.3V, (unless otherwise noted)

Table 1.4 Electrical Characteristics

Parameter	Symbol	Condition	Min	Тур	Max	Unit
VIN Supply Voltage						
Photovoltaic Voltage Input	V _{IN}		4	5.3	7.2	V
Quiescent Current Normal Mode	Icc-norm	I_{LOAD} = 0A, no switching EN \geq 2.2V (HIGH)		3		mA
Quiescent Current Disabled Mode	I _{CC-DISABLE}	EN = 0V		10	50	μΑ
VBAT Leakage						
Leakage Current From Battery	I _{BAT-LEAK}	$EN = 0V, V_{VBAT} = 4.1V$			10	μΑ
Reverse Current	I _{BAT-BACK}	V_{VBAT} > VIN, V_{VBAT} = 4.1V, Tj < 85°C			10	μΑ

²⁾ For best performance, use a low ESR ceramic capacitor.

³⁾ For best performance, use a low ESR ceramic capacitor. If C_{IN} is not a low ESR ceramic capacitor, add a 0.1µF ceramic capacitor in parallel to C_{IN}.



Parameter	Symbol	Symbol Condition		Тур	Max	Unit
VIN Under-Voltage Lockout						
Input Supply Under-Voltage Threshold	V _{IN-UV}	V _{IN} increasing		3.15		V
Input Supply Under-Voltage Threshold Hysteresis	V _{IN-UV_HYST}		100	200		mV
OSC						
Oscillator Frequency	fosc		0.9	1	1.1	MHz
NFLT Open Drain Output						
High-Level Output Leakage	I _{OH-NFLT}	$V_{NFLT} = 5.3V$		0.1		μA
Low-Level Output Voltage	V _{OL-NFLT}	I _{NFLT} = -1mA			0.4	V
EN/SCL/SDA Input Voltage Ti	nresholds					
High Level Input Voltage	V _{IH}		2.2			V
Low Level Input Voltage	V _{IL}				0.8	V
Input Hysteresis- EN, SCL, SDA Pins	V _{HYST}			200		mV
Innut I calcare . EN Die	I _{IN-EN}	V _{EN} =VIN		0.1		μA
Input Leakage – EN Pin		V _{EN} =0V		-2.0		μA
Innut Lockogo CCL Din		V _{SCL} =VIN		55		μA
Input Leakage – SCL Pin	I _{IN-SCL}	V _{SCL} =0V		-0.1		μA
Input Lookage CDA Din	I	V _{SDA} =VIN		0.1		μA
Input Leakage – SDA Pin	I _{IN-SDA}	V _{SDA} =0V		-0.1		μA
Low-Level Output Voltage	V _{OL-SDA}	$I_{SDA} = -1mA$			0.4	V
Thermal Shutdown						
Thermal Shutdown Junction Temperature	T _{SD}		150	170		°C
TSD Hysteresis	T _{SD-HYST}			10		°C
Pre-Charge End						
Pre-charge Voltage Threshold	V _{PRECHG}		2.9	3.0	3.1	V
Pre-charge Voltage Hysteresis	V _{PC-HYST}			70		mV
Charge Restart						
Voltage Below Termination for Charging Restart	V _{RESTART}			100		mV



Parameter	Symbol	Condition	Min	Тур	Max	Unit
Charging Regulator with Lour	=4.7µH and	C _{OUT} =4.7µF				
Output Current Limit Tolerance in Full-Charge Mode	I _{BAT-FC}	I _{BAT} is user programmable; see Table 2.5.	I _{BAT} - 10%	I _{BAT}	I _{BAT} + 10%	А
Termination Voltage Tolerance in Top-Off Mode	V _{ВАТ-ТО}	I _{CHG} = 0.1C, 0°C < Tj < 85°C V _{BAT} is user programmable; see section 2.4.	V _{BAT} - 1%	V _{BAT}	V _{BAT} + 1%	V
Top-Off Mode Time Out	t _{TO}		0		120	Minutes
Full-Charge Timer	t _{FC}		200		1400	Minutes
Timer Accuracy	t _{ACC}		-10%		+10%	
High Side (HS) Switch On Resistance	Б	I _{SW} = -1A, T _J =25°C		200		mΩ
Low Side (LS) Switch On Resistance	R _{DSON}	I _{SW} = 1A, T _J =25°C		250		mΩ
Maximum Output Current	I _{BAT}			1.5		А
Over-Current Detection	locd	HS switch current	2.5			А
V _{BAT} Over-Voltage Threshold	V _{BAT-OV}		101% V _{BAT}	102% V _{BAT}	103% V _{BAT}	V
Maximum Duty Cycle	DUTY _{MAX}			98		%
Thermistor						
VTH_REF Output Voltage	V_{VTH_REF}	$I_{VT_REF} = 2\mu A$ to $100\mu A$		1.8		V
Thermistor: 10kΩ Temperature	Thresholds -	- β=3434K				
0°C VTHERM Threshold (0°C)	0°C	Decreasing Temperature		75.6		%VTH_REF
0°C VTHERM Threshold with Hysteresis (10°C)	0°C _{HYST}	Increasing Temperature		66.5		%VTH_REF
10°C VTHERM Threshold (10°C)	10°C	Decreasing Temperature		66.2		%VTH_REF
10°C VTHERM Threshold with Hysteresis (11°C)	10°C _{HYST}	Increasing Temperature		65.4		%VTH_REF
45°C VTHERM Threshold (45°C)	45°C	Increasing Temperature		34.5		%VTH_REF
45°C VTHERM Threshold with Hysteresis (44°C)	45°C _{HYST}	Decreasing Temperature		35.3		%VTH_REF
50°C VTHERM Threshold (50°C)	50°C	Increasing Temperature		30.8		%VTH_REF
50°C VTHERM Threshold with Hysteresis (49°C)	50°C _{HYST}	Decreasing Temperature		31.5		%VTH_REF



Parameter	Symbol	Condition	Min	Тур	Max	Unit
60°C VTHERM Threshold (60°C)	60°C	Increasing Temperature		24.9		%VTH_REF
60°C VTHERM Threshold with Hysteresis (50°C)	60°C _{HYST}	Decreasing Temperature		30.8		%VTH_REF
Thermistor: 100KΩ Temperatur	e Thresholds	s – β=4311K				
0°C VTHERM Threshold (0°C)	0°C	Decreasing Temperature		80.5		%VTH_REF
0°C VTHERM Threshold with Hysteresis (10°C)	0°C _{HYST}	Increasing Temperature		69.8		%VTH_REF
10°C VTHERM Threshold (10°C)	10°C	Decreasing Temperature		69.8		%VTH_REF
10°C VTHERM Threshold with Hysteresis (11°C)	10°C _{HYST}	Increasing Temperature		68.6		%VTH_REF
45°C VTHERM Threshold (45°C)	45°C	Increasing Temperature		31.3		%VTH_REF
45°C VTHERM Threshold with Hysteresis (44°C)	45°C _{HYST}	Decreasing Temperature		32.3		%VTH_REF
50°C VTHERM Threshold (50°C)	50°C	Increasing Temperature		27.0		%VTH_REF
50°C VTHERM Threshold with Hysteresis (49°C)	50°C _{HYST}	Decreasing Temperature		27.8		%VTH_REF
60°C VTHERM Threshold (60°C)	60°C	Increasing Temperature		19.4		%VTH_REF
60°C VTHERM Threshold with Hysteresis (50°C)	60°C _{HYST}	Decreasing Temperature		27.0		%VTH_REF



1.5. I²C[™] Interface Timing Requirements

Electrical characteristics T_J = -40°C to 125°C, VIN = 5.3V. See Figure 2.5 for an illustration of the timing specifications given in Table 1.5.

Table 1.5 f^2C^{TM} Interface Timing Characteristics

Devenuetes	Cumbal	Standa	rd Mode	Fast Mode 1)		Unit
Parameter	Symbol	Min	Max	Min	Max	Unit
I ² C™ Clock Frequency	f _{scl}	0	100	0	400	kHz
I ² C™ Clock High Time	t _{sch}	4		0.6		μs
I ² C™ Clock Low Time	t _{scl}	4.7		1.3		μs
I ² C™ Tolerable Spike Time ²⁾	t _{sp}	0	50	0	50	ns
I ² C™ Serial Data Setup Time	t _{sds}	250		250		ns
I ² C™ Serial Data Hold Time	t _{sdh}	0		0		μs
I ² C™ Input Rise Time ²⁾	t _{icr}		1000		300	ns
I ² C™ Input Fall Time ²⁾	t _{icf}		300		300	ns
I ² C TM Output Fall Time; 10pF to 400pF Bus ²⁾	t _{ocf}		300		300	ns
I ² C [™] Bus Free Time Between Stop and Start	t _{buf}	4.7		1.3		μs
I ² C [™] Start or Repeated Start Condition Setup Time	t _{sts}	4.7		0.6		μs
I ² C [™] Start or Repeated Start Condition Hold Time	t _{sth}	4		0.6		μs
I ² C [™] Stop Condition Setup Time ²⁾	t _{sps}	4		0.6		μs

¹⁾ The I²C[™] interface will operate in either standard or fast mode.

²⁾ Parameter not tested in production.

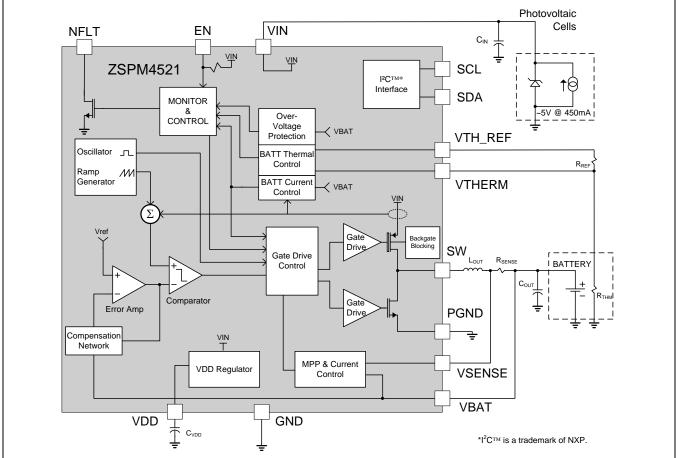


2 **Functional Description**

The ZSPM4521 is a fully-integrated Li-Ion battery charger IC based on a highly-efficient switching topology. It includes a maximum power point tracking (MPPT) function to optimize its input voltage in order to extract the maximum possible power from photovoltaic (PV) cells. It is configurable for termination voltage, charge current, and additional variables to allow optimum charging conditions for a wide range of Li-Ion batteries. A 1MHz internal switching frequency facilitates low-cost LC filter combinations. Figure 2.1 provides a block diagram.

When the battery voltage is below 3.0V, the ZSPM4521 enters a pre-charge state and applies a small, programmable charge current to safely charge the battery to a level for which full-charge current can be applied. Once the Full-Charge Mode has been initiated, the ZSPM4521 will maximize available charge current to the battery by adjusting its duty cycle to regulate its input voltage to the MPP voltage of the photovoltaic (PV) cell. If sufficient current is available from the PV cell to exceed the safe 1C charge rate of the battery, then the programmable 1C current limit function will take precedence over the MPPT control function and the PV cell voltage will rise above the MPP value.

Figure 2.1 ZSPM4521 Block Diagram





When the battery voltage has increased enough to go into maintenance mode, the PWM control loop will force a constant voltage across the battery. Once in Constant Voltage Mode, current is monitored to determine when the battery is fully charged. See Figure 2.2 for a diagram of the charging states.

The regulation voltage as well as the 1C charging current can be set to change based on the battery temperature. There are four temperature ranges for which the regulation voltage can be set independently: 0°C to 10°C, 10°C to 45°C, 45°C to 50°C, and 50°C to 60°C. The ZSPM4521 will stop charging if the temperature passes the descending temperature threshold at 0°C or the ascending threshold at 60°C. These thresholds have 10 degrees of hysteresis. The intermediate points have 1 degree of hysteresis.

2.1. Internal Protection

2.1.1. VIN Under-Voltage Lockout

The device is held in the off state until the EN pin voltage is HIGH (≥ 2.2V) and VIN reaches 3.15V (typical). There is a 200mV hysteresis on this input, which requires the input to fall below 2.95V (typical) before the device will disable.

2.1.2. Internal Current Limit

The current through the inductor L_{OUT} is sensed on a cycle-by-cycle basis and if the current limit (I_{OCD}; see section 1.4) is reached, the ZSPM4521 will abbreviate the cycle. The current limit is always active when the regulator is enabled.

2.1.3. Thermal Shutdown

If the junction temperature of the ZSPM4521 exceeds 170°C (typical), the SW output will tri-state to protect the device from damage. The NFLT and all other protection circuitry will stay active to inform the system of the failure mode. Once the device cools to 160°C (typical), the device will attempt to start up again. If the device reaches 170°C, the shutdown/restart sequence will repeat.

2.1.4. VBAT Over-Voltage Protection

The ZSPM4521 has a battery protection circuit designed to shut down the charging profile if the battery voltage is greater than the termination voltage. The termination voltage can change based on user programming, so the protection threshold is set to 2% above the termination voltage. Shutting down the charging profile puts the ZSPM4521 in a fault condition.



2.2. Fault Handling

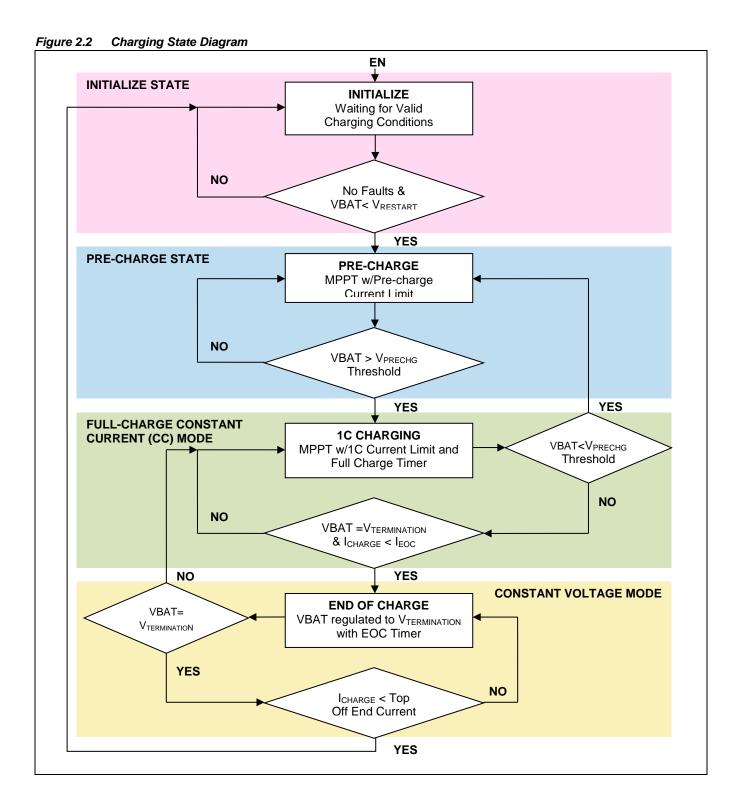
2.2.1. **NFLT Pin Functionality**

In the event of a battery over-voltage, the battery temperature being outside of the safe charging range, or the full charge timer expiring, charging stops and the NFLT pin is pulled low. When the fault condition is no longer present, the device will enter the INITIALIZE state (see Figure 2.2), but the NFLT pin will remain low until the STATUS register (00_{HEX}) is read (see Table 2.2). When the STATUS register is read, the NFLT pin will go high until a new fault is detected.

2.2.2. Other Faults

When an open thermistor, thermal shutdown, VIN under-voltage, or top-off time-out are detected, charging immediately stops and the corresponding bit in the STATUS register (00_{HEX}) is set. The device will enter the INITIALIZE state until the fault is no longer detected.





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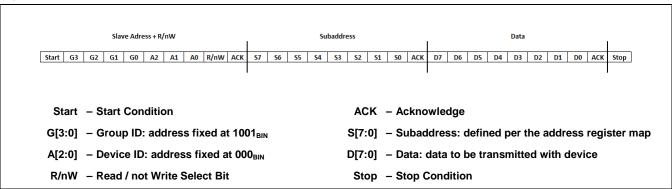
2.3. Serial Interface

The ZSPM4521 features an I²C[™] slave interface that offers advanced control and diagnostic features. It supports standard and fast mode data rates and auto-sequencing, and it is compliant to I²C[™] standard version 3.0.

I²C™ operation offers configuration control for termination voltages, charge currents, and charge timeouts. This configurability allows optimum charging conditions in a wide range of Li-Ion batteries. I²C™ operation also offers fault and warning indicators. Whenever a fault is detected, the associated status bit in the STATUS register is set and the NFLT pin is pulled low. Whenever a warning is detected, the associated status bit in the STATUS register is set, but the NFLT pin is not pulled low. Reading the STATUS register resets the fault and warning status bits, and the NFLT pin is released after all fault status bits have been reset.

2.3.1. I²C[™] Subaddress Definition

Figure 2.3 Subaddress in f²C™ Transmission



2.3.2. I²C[™] Bus Operation

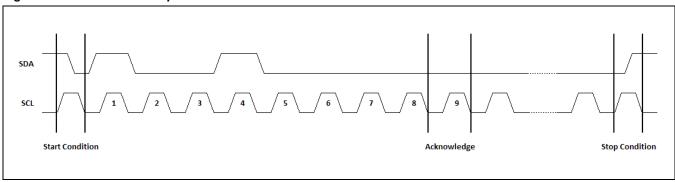
The ZSPM4521's I²C[™] is a two-wire serial interface; the two lines are serial clock (SCL) and serial data (SDA) (see Figure 2.4). SDA must be connected to a positive supply (e.g., the VDD pin) through an external pull-up resistor. The devices communicating on this bus can drive the SDA line low or release it to high impedance. To ensure proper operation, setup and hold times must be met (see Table 1.5). The device that initiates the I²C[™] transaction becomes the master of the bus.

Communication is initiated by the master sending a START condition, which is a high-to-low transition on SDA while the SCL line is high. After the START condition, the device address byte is sent, most significant bit (MSB) first, including the data direction bit (read = 1; write = 0). After receiving the valid address byte, the device responds with an acknowledge (ACK). An ACK is a low on SDA during the high of the ACK-related clock pulse. On the I²CTM bus, during each clock pulse, only one data bit is transferred. The data on the SDA line must remain stable during the high pulse of the clock period, as changes in the data line at this time are interpreted as START or STOP control conditions. A low-to-high transition on SDA while the SCL input is high indicates a STOP condition and is sent by the master.



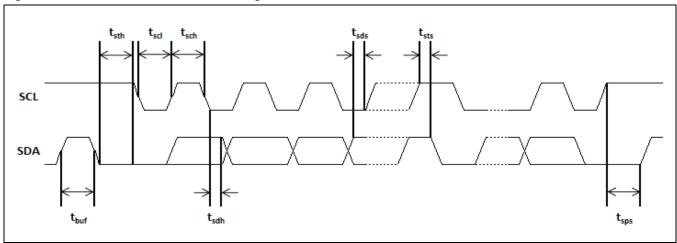
Any number of data bytes can be transferred from the transmitter to receiver between the START and the STOP conditions. Each byte of eight bits is followed by one ACK bit from the receiver. The SDA line must be released by the transmitter before the receiver can send an ACK bit. The receiver that acknowledges must pull down the SDA line during the ACK clock pulse, so that the SDA line is stable low during the high pulse of the ACK-related clock period. When a slave receiver is addressed, it must generate an ACK after each byte is received. Similarly, the master must generate an ACK after each byte that it receives from the slave transmitter. An end of data is signaled by the master receiver to the slave transmitter by not generating an acknowledge after the last byte has been clocked out of the slave. This is done by the master receiver by holding the SDA line high. The transmitter must then release the data line to enable the master to generate a STOP condition.

Figure 2.4 I²C™ Start / Stop Protocol



See Table 1.5 for the definitions and specifications for the timing parameters labeled in Figure 2.5.

Figure 2.5 I²C[™] Data Transmission Timing





2.4. Status and Configuration Registers

Table 2.1 Register Descriptions (Device Address = 48_{HEX})

Register	Address	Name	Default	Description
0	00 _{HEX}	STATUS	00 _{HEX}	Status bit register
1	N/A	N/A	N/A	Register not implemented
2	02 _{HEX}	CONFIG1 1)	EEPROM	Configuration register
3	03 _{HEX}	CONFIG2 1)	EEPROM	Configuration register
4	04 _{HEX}	CONFIG3 1)	EEPROM	Configuration register
5	05 _{HEX}	CONFIG4 1)	EEPROM	Configuration register
6	06 _{HEX}	CONFIG5 1)	EEPROM	Configuration register
7-16	N/A	N/A	N/A	Registers not implemented
17	11 _{HEX}	CONFIG_ENABLE	00нех	Enable configuration register access
18	12 _{HEX}	EEPROM_CTRL 1)	00 _{HEX}	EEPROM control register

⁾ CONFIGx and EEPROM_CTRL registers are only accessible when the CONFIG_ENABLE register is written with the EN_CFG bit set to 1 (see Table 2.8).

Table 2.2 STATUS Register—Address 00_{HEX}

Note: All of the STATUS register bits are READ-only.

DATA BIT	D7	D6	D5	D4	D3	D2	D1	D0	
FIELD NAME	BATT_OV	1C_TO	TEMP_0C	TEMP_60C	TSD	TOP_TO	VIN_UV	TH_OPEN	
FIELD N	AME		BIT DEFINITION 1)						
BATT_OV		VBAT over-voltage.							
1C_TO		Full charge timer has timed out.							
TEMP_0C Thermistor indicates ba				ery temperatu	re < 0°C.				
TEMP_60C		Thermistor indicates battery temperature > 60°C.							
TSD		Thermal sh	utdown.						
TOP_TO Top-off timer has timed out.									
VIN_UV	YIN_UV VIN under-voltage.								
TH_OPEN		Thermistor open (battery not present).							

Faults are defined as BATT_OV, 1C_TO, TEMP_OC, and TEMP_60C. Warnings are defined as TSD, TOP_TO, VIN_UV, and TH_OPEN. Faults cause the NFLT pin to be pulled low. Warnings do not cause the NFLT pin to be pulled low. All status bits are cleared after STATUS register read access. The NFLT pin will go to high impedance (open-drain output) after the STATUS register has been read and all status bits have been reset.



Table 2.3 Configuration Register CONFIG1—Address 02_{HEX}

Note: All of the CONFIG1 register bits are READ/WRITE.

DATA BIT	D7	D6	D5	D4	D3	D2	D1	D0
FIELD NAME	PRE_C	HRG[1:0] V_TERM_0_10[2:0] V_TERM_10_45[2			[2:0]			
FIELD N	AME		BIT DEFINITION					
PRE_CHRG[1:0	O] ¹⁾	Pre-chargin	g configuratio	01 _{ві} 10 _{ві}	_N – 50mA _N – 100mA _N – 185mA _N – 370mA			
V_TERM_0_10	[2:0] 2) Voltage termination: 0-10°C configuration		0		_{ВІN} – 3.94V _{ВІN} – 4.00V	_	0 _{BIN} – 4.12V 1 _{BIN} – 4.15V	
V_TERM_10_4	5[2:0] ²⁾	Voltage terr 10-45°C co	ination: 010 _{Blf}		_{BIN} – 4.05V _{BIN} – 4.10V		O _{BIN} – 4.18V 1 _{BIN} – Invalid s	setting

¹⁾ PRE_CHRG Note: Maximum output current when $V_{BAT} < 3.0V$.

Table 2.4 Configuration Register CONFIG2—Address 03_{HEX}

Note: All of the CONFIG2 register bits are READ/WRITE.

DATA BIT	D7	D6	D5	D4	D3	D2	D1	D0
FIELD NAME	EOC	[1:0] V_TERM_45_50[2:0] V_TERM_50_6				ERM_50_60	[2:0]	
FIELD N	AME			BIT DEF	INITION			
EOC[1:0] 1)		End of char	ge configurati	figuration $00_{\text{BIN}} - 50\text{mA}$ $01_{\text{BIN}} - 100\text{mA}$ $10_{\text{BIN}} - 185\text{mA}$ $11_{\text{BIN}} - 370\text{mA}$				
V_TERM_45_5			Voltage termination: 45-50°C configuration		00 _{BIN} – 3.94V 01 _{BIN} – 4.00V		00 _{BIN} - 4.12V 01 _{BIN} - 4.15V	
V_TERM_50_60[2:0] ²⁾ Voltage termination: 50-60°C configuration			10 _{BIN} – 4.05V 11 _{BIN} – 4.10V	110 _{BIN} – 4.18V 111 _{BIN} – Invalid setting				

¹⁾ EOC Note: Maximum output current when $V_{BAT} \ge 3.0V$.

²⁾ V_TERM Note: There are separate settings for battery temperatures 0-10°C, 10-45°C, 45-50°C, and 50-60°C (see Table 2.4 for 45-50°C and 50-60°C). For <0°C and >60°C, charging is disabled and a fault is set.

²⁾ V_TERM Note: There are separate settings for battery temperatures 0-10°C, 10-45°C, 45-50°C, and 50-60°C (see Table 2.3 for 0-10°C and 10-45°C). For <0°C and >60°C, charging is disabled and a fault is set.



Table 2.5 Configuration Register CONFIG3—Address 04_{HEX}

Note: All of the CONFIG3 register bits are READ/WRITE.

DATA BIT	D7	D6	D5	D4	D3	D2	D1	D0
FIELD NAME	NAME MAX_CHRG_CURR_0_10[3:0] MAX_CHRG_CURR_10_45[3:0]			:0]				
FIELD NAME				BIT DEFIN	IITION			
MAX_CHRG_C	CURR_0_10[3		aximum charge 10°C configura		0000 _{BIN} - 0001 _{BIN} - 0010 _{BIN} -	100mA 200mA	1000 _{BIN} - 8 1001 _{BIN} - 9 1010 _{BIN} - 1	00mA 000mA
MAX_CHRG_C	CHRG_CURR_10_45[3:0] 1) Maximum charge current; 10-45°C configuration			0011 _{BIN} — 0100 _{BIN} — 0101 _{BIN} — 0110 _{BIN} — 0111 _{BIN} —	400mA 500mA 600mA	1011 _{BIN} — 1100mA 1100 _{BIN} — 1200mA 1101 _{BIN} — 1300mA 1110 _{BIN} — 1400mA 1111 _{BIN} — 1500mA		
1) MAX_CHRO	_		arate settings for			•	°C, and 50-60°	C (see Table

⁾ MAX_CHRG_CURR Note: There are separate settings for battery temperatures 0-10°C, 10-45°C, 45-50°C, and 50-60°C (see Table 2.6 for 45-50°C and 50-60°C). For <0°C and >60°C, charging is disabled and a fault is set.

Table 2.6 Configuration Register CONFIG4—Address 05_{HEX}

Note: All of the CONFIG4 register bits are READ/WRITE.

DATA BIT	D7	D6	D5	D4	D3	D2	D1	D0
FIELD NAME	MA	X_CHRG_C	URR_45_50[3	3:0]	MA	AX_CHRG_C	JRR_50_60[3	3:0]
FIELD NAME			BIT DEFINITION					
MAX_CHRG_C	URR_45_50[- 1	aximum charge -50°C configu		0000 _{BIN} - 0001 _{BIN} - 0010 _{BIN} -	100mA 200mA	1000 _{BIN} - 8 1001 _{BIN} - 9 1010 _{BIN} - 1 1011 _{BIN} - 1	00mA 000mA
MAX_CHRG_C	:URR_50_60[Maximum charge current: 50-60°C configuration			0100 _{BIN} - 400mA 1100 _{BIN} - 1200m. 0101 _{BIN} - 500mA 1101 _{BIN} - 1300m. 0110 _{BIN} - 600mA 1110 _{BIN} - 1400m. 0111 _{BIN} - 700mA 1111 _{BIN} - 1500m.		
, –	_	•	arate settings for For <0°C and >6			•	°C, and 50-60°	С



Table 2.7 Configuration Register CONFIG5—Address 06_{HEX}

Note: All of the CONFIG5 register bits are READ/WRITE.

DATA BIT	D7	D6	D5	D4	D3	D2	D1	D0	
FIELD NAME	TOP_END	TH		TOP_TO[2:0]			1C_TO[2:0]		
FIELD NAME	'		BIT DEFINITION						
TOP_END 1)		=	Top-off end configuration $0_{BIN} - 25mA$						
TH ²⁾		Thermisi 0 _{BIN} – 10	Thermistor configuration $0_{BIN}-10k\Omega \\ 1_{BIN}-100k\Omega$						
TOP_TO[2:0] ³		000 _{BIN} — 001 _{BIN} — 010 _{BIN} — 011 _{BIN} — 100 _{BIN} — 110 _{BIN} —	mer time out 0 minutes 20 minutes 40 minutes 60 minutes 80 minutes 100 minutes 120 minutes Disable time	configuration					
1C_TO[2:0] ⁴⁾		000 _{BIN} — 001 _{BIN} — 010 _{BIN} — 011 _{BIN} — 100 _{BIN} — 110 _{BIN} —	ge timer time Disable full c 200 minutes 400 minutes 600 minutes 800 minutes 1000 minutes 1200 minutes	S S	ion				

¹⁾ TOP_END Note: Charging stops when $V_{VBAT} = V_{TERMINATION}$ and $I_{OUT} < TOP_END$

²⁾ TH Note: Setting for nominal thermistor and reference resistor value.

³⁾ TOP_TO Note: Timer starts when $V_{VBAT} = V_{TERMINATION}$ and $I_{OUT} < EOC$.

^{4) 1}C_TO Note: Timer starts when $V_{VBAT} > 3.0V$.



Table 2.8 Enable Configuration Register CONFIG_ENABLE—Address 11_{HEX}

Note: The reset value for all of the CONFIG_ENABLE register bits is 0.

DATA BIT	D7	D6	D5	D4	D3	D2	D1	D0
FIELD NAME	Not used	Not used	Not used	Not used	Not used	Not used	Not used	EN_CFG
READ/WRITE	R	R	R	R	R	R	R	R/W
FIELD NAME			BIT DEFINITION					
EN_CFG		(address 0 _{BIN} - D	access contro ses 02 _{HEX} to 0 disable access nable access	;	uration registe	rs CONFIG1	through CONI	FIG5

Table 2.9 EEPROM Control Register EEPROM_CTRL—Address 12_{HEX}

Note: The reset value for all of the EEPROM_CTRL register bits is 0.

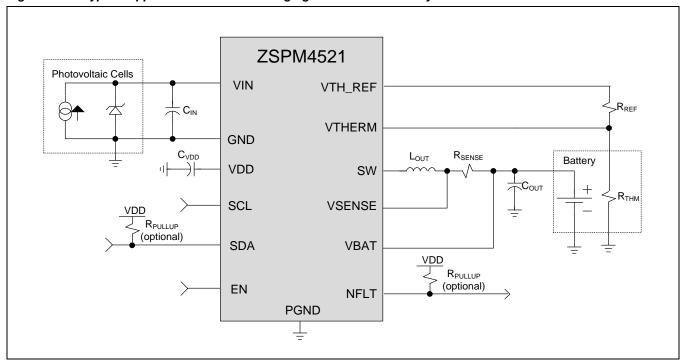
DATA BIT	D7	D6	D5	D4	D3	D2	D1	D0
FIELD NAME	Not used	Not used	Not used	Not used	Not used	Not used	Not used	EE_PROG
READ/WRITE	R	R	R	R	R	R	R	R/W
FIELD NAME			BIT DEFINITION					
EE_PROG 1)	EE_PROG 1) EEPROM program control bit for configuration registers CONFIG1 through CONFIG5 (addresses 02 _{HEX} to 06 _{HEX}) 0 _{BIN} - Disable EEPROM programming 1 _{BIN} - Enable EEPROM programming with data from configuration registers CONFIG1 through CONFIG5 (addresses 02 _{HEX} to 06 _{HEX})							
EE_PROG Note: Inputs VIN and EN must be present for 200ms.								



3 Application Circuits

3.1. Typical Application Circuit

Figure 3.1 Typical Application Circuit for Charging a Lithium-Ion Battery via Photovoltaic Cells



3.2. Selection of External Components

Note that the internal compensation is optimized for a $4.7\mu\text{F}$ output capacitor (C_{OUT}) and a $4.7\mu\text{H}$ output inductor (L_{OUT}). Table 1.3 provides recommended ranges for most of the following components.

3.2.1. C_{OUT} Output Capacitor

To keep the output ripple low, a low ESR (less than $35m\Omega$) ceramic capacitor is recommended for the $4.7\mu F$ output filter capacitor. The ESR should not exceed $100m\Omega$.

3.2.2. L_{OUT} Output Inductor

For best performance, an inductor with a saturation current rating higher than the maximum V_{OUT} load requirement plus the inductor current ripple should be used for the 4.7 μ H output filter inductor.

3.2.3. C_{IN} Bypass Capacitor for Input from Photovoltaic Source

For best performance, a low ESR ceramic capacitor should be used for the $10\mu F$ input supply bypass capacitor. If it is not a low ESR ceramic capacitor, a $0.1\mu F$ ceramic capacitor should be added in parallel to C_{IN} .



3.2.4. C_{VDD} Bypass Capacitor for VDD Internal Reference Voltage Output

For best performance, a low ESR ceramic capacitor should be used for the 100nF bypass capacitor from the VDD pin to ground.

3.2.5. R_{SENSE} Output Sensing Resistor

The typical value for the output sensing resistor is $50m\Omega$.

3.2.6. Pull-up Resistors

For proper function of the I²C[™] interface, the SDA pin must be connected to a positive supply (e.g., the VDD pin) through an external pull-up resistor.

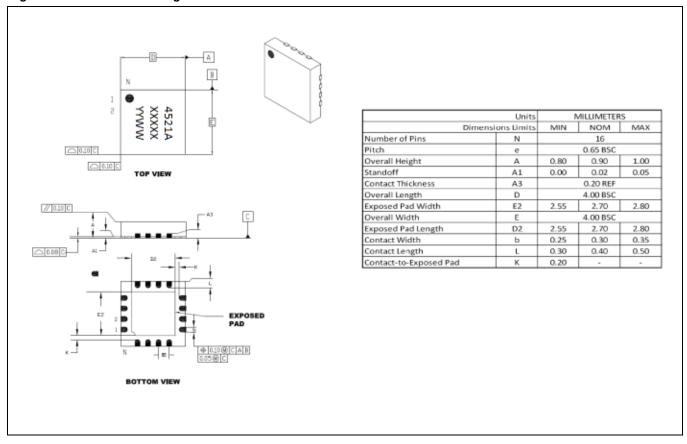
For proper function of the fault-warning signal on the NFLT pin, it must be connected to a positive supply (VDD) through an external pull-up resistor.



4 Pin Configuration and Package

4.1. ZSPM4521 Package Dimensions

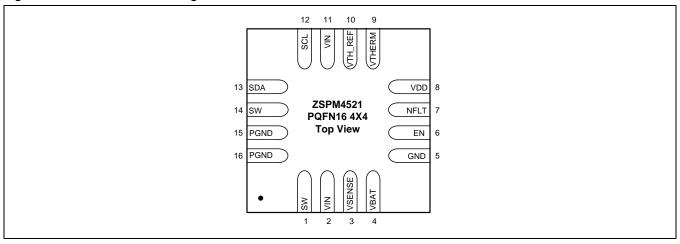
Figure 4.1 PQFN-16 Package Dimensions





4.2. Pin-Out Assignments

Figure 4.2 ZSPM4521 Pin Assignments



4.3. Pin Description for 16-Pin PQFN (4 x 4 mm)

Table 4.1 Pin Description

Pin#	Name	Function	Description		
1	SW	Switching Voltage Node	Connect to L _{OUT} 4.7µH (typical) inductor. Also connect to additional SW pin 14.		
2	VIN	Photovoltaic Input Voltage	Input voltage from the photovoltaic cell. Also connect to C_{IN} . Also connect to additional VIN pin 11.		
3	VSENSE	Current Sense Positive Input	Positive input for the MPPT current loop.		
4	VBAT	Output Voltage	Regulator feedback input.		
5	GND	GND	Primary ground for the majority of the device except the low-side power FET.		
6	EN	Enable Input	When EN is high (≥ 2.2V), the device is enabled. Ground the pin to disable the device. Includes internal pull-up.		
7	NFLT	Inverted Fault	Open-drain output.		
8	VDD	Internal 3.3V Supply Output	Connect to a 100nF capacitor to GND.		
9	VTHERM	Battery Temperature Sensor Minus Node	Negative node for the thermistor, which must be located in close proximity to the battery.		



Pin#	Name	Function	Description
10	VTH_REF	Battery Temperature Sensor Positive Node	Positive node for the thermistor, which must be located in close proximity to the battery.
11	VIN	Photovoltaic Input Voltage	Additional VIN pin for input voltage from the photovoltaic cell; connect to VIN pin 2.
12	SCL	Clock Input	I ² C™ clock input.
13	SDA	Data Input/Output	I ² C™ data (open-drain output).
14	SW	Switching Voltage Node	Additional SW pin; connect to SW pin 1.
15	PGND	Power GND	GND supply for internal low-side FET/integrated diode. Also connect to additional PGND pin 16.
16	PGND	Power GND	GND supply for internal low-side FET/integrated diode. Also connect to additional PGND pin 15.

4.4. Package Markings

Figure 4.3 Marking Diagram 16-Pin PQFN (4 x 4 mm)

4521A XXXXX oYYWW XXXXX: Lot Number (last five digits)

O: Pin 1 mark

YY: Year

WW: Work Week



5 Layout Recommendations

To maximize the efficiency of this package for application on a single layer or multi-layer PCB, certain guidelines must be followed when laying out this part on the PCB.

5.1. Multi-Layer PCB Layout

The following are guidelines for mounting the exposed pad ZSPM4521 on a multi-layer PCB with ground a plane. In a multi-layer board application, the thermal vias are the primary method of heat transfer from the package thermal pad to the internal ground plane. The efficiency of this method depends on several factors, including die area, number of thermal vias, and thickness of copper, etc.

Figure 5.1 Package and PCB Land Configuration for Multi-Layer PCB

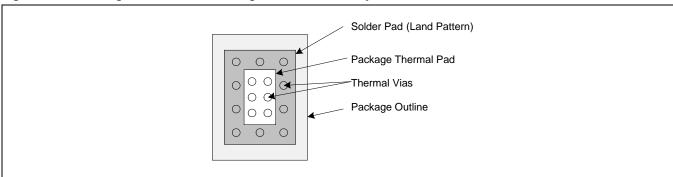


Figure 5.2 JEDEC Standard FR4 Multi-Layer Board – Cross-Sectional View

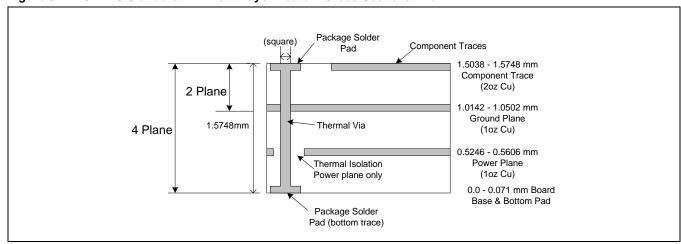




Figure 5.3 is a representation of how the heat can be conducted away from the die using an exposed pad package. Each application will have different requirements and limitations, and therefore the user should use sufficient copper to dissipate the power in the system. The output current rating for the linear regulators might need to be de-rated for higher ambient temperatures. The de-rated value will depend on calculated worst-case power dissipation and the thermal management implementation in the application.

Mold compound
Die
Epoxy Die attach
Exposed pad
Solder

5% - 10% Cu coverage

Thermal Vias with Cu plating
Ground Layer, 1oz Cu
90% Cu coverage

Signal Layer, 1oz Cu
20% Cu coverage

Bottom Layer, 2oz Cu

Figure 5.3 Conducting Heat Away from the Die using an Exposed Pad Package

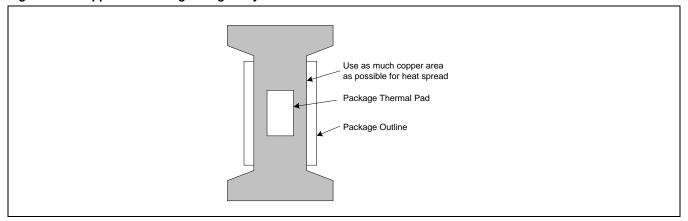
5.2. Single-Layer PCB Layout

Layout recommendations for a single-layer PCB: Utilize as much copper area for power management as possible. In a single-layer board application, the thermal pad is attached to a heat spreader (copper areas) by using a low thermal impedance attachment method (solder paste or thermal conductive epoxy).

In both of the methods mentioned above, it is advisable to use as much copper trace as possible to dissipate the heat.



Figure 5.4 Application Using a Single-Layer PCB



Important: If the attachment method is NOT implemented correctly, the functionality of the product is NOT guaranteed. Power dissipation capability will be adversely affected if the device is incorrectly mounted onto the circuit board.

6 Ordering Information

Ordering Code	Description	Package
ZSPM4521AA1W	ZSPM4521 High Efficiency Li-Ion Battery Charger for Photovoltaic Sources	16-pin PQFN / 7" Reel (1000 parts)
ZSPM4521AA1R	ZSPM4521 High Efficiency Li-Ion Battery Charger for Photovoltaic Sources	16-pin PQFN / 13" Reel (3300 parts)
ZSPM4521KIT	ZSPM4521 Evaluation Kit	

7 Related Documents

Document
ZSPM4521 Feature Sheet
ZSPM4521 Evaluation Kit Description
ZSPM4521 Application Note – Solar Powered Battery Management and Charging Solutions

Visit IDT's website www.IDT.com or contact your nearest sales office for the latest version of these documents.



8 Document Revision History

Revision	Date	Description
1.00	February 14, 2013	First release.
1.01	October 3, 2014	Revision of specification for VTH_REF output voltage in Table 1.4. Updates for contact information and imagery on cover and headers.
	January 27, 2016	Changed to IDT branding.



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